

Title (en)

METHOD FOR THERMAL SELF-HEALING OF AN SiC SEMICONDUCTOR AREA DOPED BY MEANS OF IMPLANTATION AND A SiC BASED SEMICONDUCTOR COMPONENT

Title (de)

VERFAHREN ZUM THERMISCHEN AUSHEILEN EINES DURCH IMPLANTATION DOTIERTEN SiC-HALBLEITERGEBIETES UND HALBLEITERBAUELEMENT AUF SiC-BASIS

Title (fr)

PROCEDE POUR L'AUTOREGENERATION THERMIQUE D'UNE REGION SEMICONDUCTRICE DE SiC DOPEE PAR IMPLANTATION ET COMPOSANT A SEMI-CONDUCTEURS A BASE DE SiC

Publication

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Application

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Abstract (en)

[origin: WO9910920A1] An SiC semiconductor area (4) doped by means of implantation is cooled from a given initial temperature of at least 1000 DEG C to a lower final temperature at a maximum cooling rate of 100 DEG C per minute. The semiconductor component contains a self-healed p-n junction (5) obtained according to said method and has a high blocking ability.

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